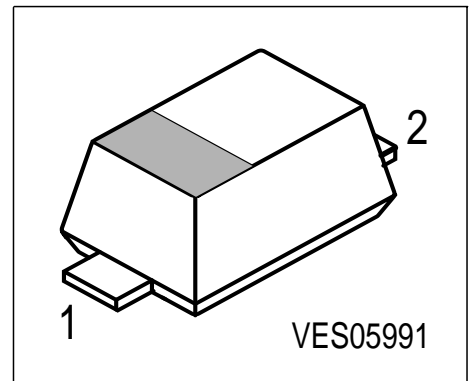


Silicon Variable Capacitance Diode

- For UHF-TV-tuners
- High capacitance ratio
- Low series inductance
- Low series resistance
- Extremely small plastic SMD package
- Excellent uniformity and matching due to "in-line" matching assembly procedure



Type	Marking	Ordering Code	Pin Configuration		Package
BB 565	C	Q62702-B0869 unmatched	1 = C	2 = A	SCD-80
BB 565	C	Q62702-B0873 in-line matched			

Maximum Ratings

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	30	V
Peak reverse voltage ($R \geq 5k\Omega$)	V_{RM}	35	
Forward current	I_F	20	mA
Operating temperature range	T_{op}	-55 ...+150	°C
Storage temperature	T_{stg}	-55 ...+150	

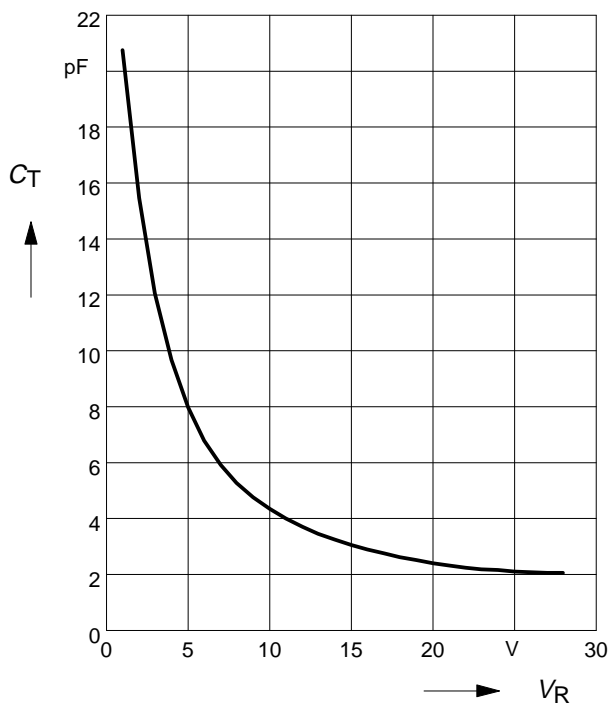
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC characteristics					
Reverse current $V_R = 30\text{ V}$	I_R	-	-	10	nA
Reverse current $V_R = 30\text{ V}, T_A = 85^\circ\text{C}$	I_R	-	-	200	
AC characteristics					
Diode capacitance $V_R = 1\text{ V}, f = 1\text{ MHz}$ $V_R = 2\text{ V}, f = 1\text{ MHz}$ $V_R = 25\text{ V}, f = 1\text{ MHz}$ $V_R = 28\text{ V}, f = 1\text{ MHz}$	C_T	18.5 13.2 1.85 1.8	20 14.8 2.07 2	21.5 16.4 2.28 2.2	pF
Capacitance ratio $V_R = 2\text{ V}, V_R = 25\text{ V}, f = 1\text{ MHz}$	C_{T2}/C_{T25}	6.3	7.2	8.1	-
Capacitance ratio $V_R = 1\text{ V}, V_R = 28\text{ V}, f = 1\text{ MHz}$	C_{T1}/C_{T28}	9	10	11	
Capacitance matching ¹⁾ $V_R = 1\text{V to }28\text{V}, f = 1\text{ MHz}, 4\text{ diodes sequence}$ $V_R = 1\text{V to }28\text{V}, f = 1\text{ MHz}, 7\text{ diodes sequence}$	$\Delta C_T/C_T$	- -	0.5 0.7	1.5 2	%
Series resistance $V_R = 3\text{ V}, f = 470\text{ MHz}$	r_s	-	0.6	-	Ω
Series inductance	L_s	-	0.6	-	nH

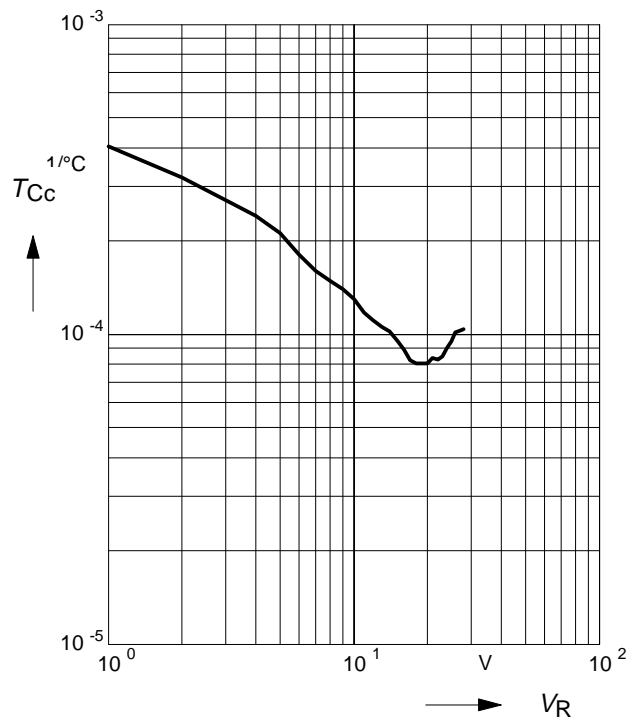
1) In-line matching. For details please refer to Application Note 047

Diode capacitance $C_T = f(V_R)$

$f = 1\text{MHz}$

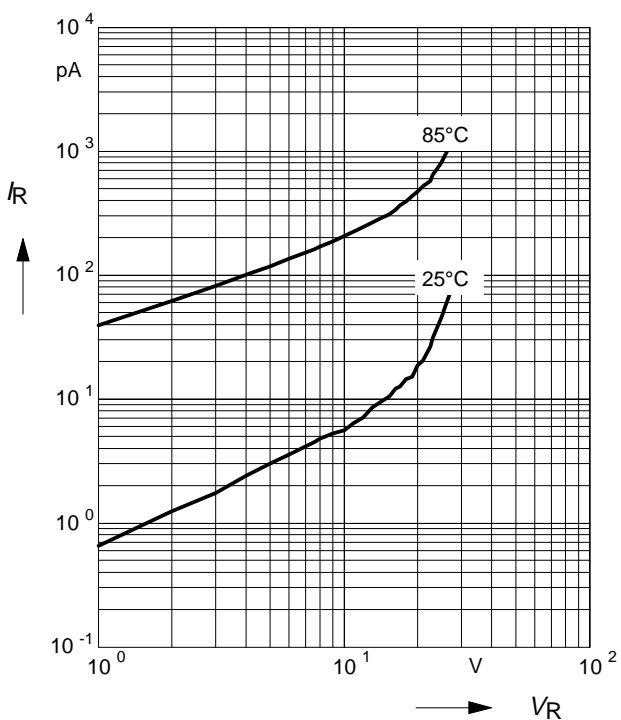


Temperature coefficient of the diode capacitance $T_{Cc} = f(V_R)$



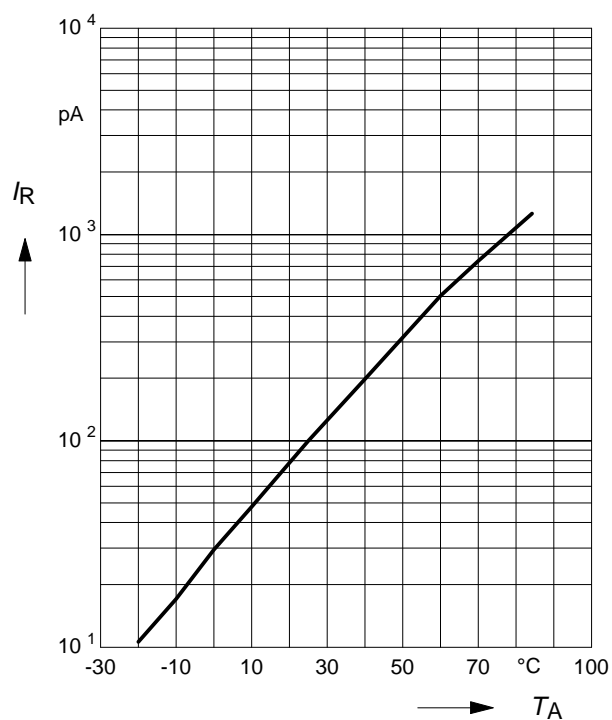
Reverse current $I_R = f(V_R)$

$T_A = \text{Parameter}$



Reverse current $I_R = f(T_A)$

$V_R = 28\text{V}$



Normalized diode capacitance

$$C_{(T_A)} / C_{(25^\circ\text{C})} = f(T_A)$$

$f = 1\text{MHz}$, $V_R = \text{Parameter}$

